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(54) **DATA STORAGE CELL, MEMORY, AND MEMORY FABRICATION METHOD THEREOF**

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ABSTRACT

The invention discloses a data storage cell. The data storage cell includes a storage structure, a first transistor, and a second transistor. A first end of the storage structure is electrically connected to a bit line. The first transistor includes a first gate, a first drain, and a first source. The second transistor includes a second gate, a second drain, and a second source. The first gate is electrically connected to the second gate. A second end of the storage structure is electrically connected to the first drain and the second drain. The first source and the second source are electrically connected to a source line.

